P-Channel 1.8 V (G-S) MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)
- 20	0.195 at V_{GS} = - 4.5 V	- 0.84
	0.260 at V_{GS} = - 2.5 V	- 0.73
	0.350 at V_{GS} = - 1.8 V	- 0.64

FEATURES

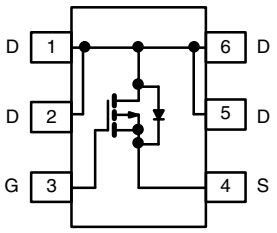
- **Halogen-free According to IEC 61249-2-21 Definition**
- TrenchFET® Power MOSFET
- Low Threshold
- Smallest LITTLE FOOT® Package: 1.6 mm x 1.6 mm
- Low 0.6 mm Profile
- Compliant to RoHS Directive 2002/95/EC

Pb-free
RoHS COMPLIANT
HALOGEN FREE

APPLICATIONS

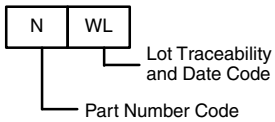
- Cell Phones and Pagers
  - Load Switch
- Battery Operated Systems

SC-89 (6-LEADS)



Top View

Marking Code



Ordering Information: Si1037X-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C, unless otherwise noted)					
Parameter		**Symbol**	**5 s**	**Steady State**	**Unit**
Drain-Source Voltage		V_{DS}	- 20		V
Gate-Source Voltage		V_{GS}	± 8		
Continuous Drain Current (T_J = 150 °C)[a]	T_A = 25 °C	I_D	- 0.84	- 0.77	A
	T_A = 70 °C		- 0.68	- 0.62	
Pulsed Drain Current		I_{DM}	- 4		
Continuous Diode Current (Diode Conduction)[a]		I_S	- 0.18	- 0.14	
Maximum Power Dissipation[a]	T_A = 25 °C	P_D	0.21	0.17	W
	T_A = 70 °C		0.13	0.10	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 150		°C

THERMAL RESISTANCE RATINGS					
Parameter		**Symbol**	**Typical**	**Maximum**	**Unit**
Maximum Junction-to-Ambient[a]	t ≤ 5 s	R_{thJA}	500	600	°C/W
	Steady State		600	720	

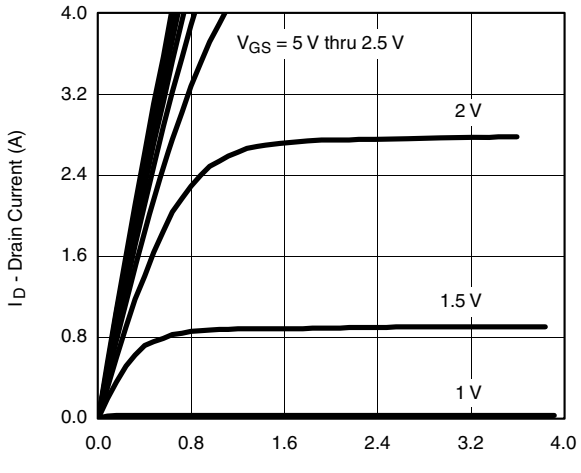
Notes:
a. Surface mounted on 1" x 1" FR4 board with minimum copper.

SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)						
Parameter	**Symbol**	**Test Conditions**	**Min.**	**Typ.**	**Max.**	**Unit**
Static						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = - 250 µA	- 0.45			V
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 8 V			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = - 20 V, V_{GS} = 0 V			- 1	µA
		V_{DS} = - 20 V, V_{GS} = 0 V, T_J = 70 °C			- 5	
On-State Drain Current[a]	$I_{D(on)}$	V_{DS} = - 5 V, V_{GS} = - 4.5 V	- 4			A
Drain-Source On-State Resistance[a]	$R_{DS(on)}$	V_{GS} = - 4.5 V, I_D = - 0.77 A		0.160	0.195	Ω
		V_{GS} = - 2.5 V, I_D = - 0.67 A		0.212	0.260	
		V_{GS} = - 1.8 V, I_D = - 0.2 A		0.290	0.350	
Forward Transconductance[a]	g_{fs}	V_{DS} = - 10 V, I_D = - 0.77 A		3.1		S
Diode Forward Voltage[a]	V_{SD}	I_S = - 0.14 A, V_{GS} = 0 V		- 0.78	- 1.2	V
Dynamic[b]						
Total Gate Charge	Q_g	V_{DS} = - 10 V, V_{GS} = - 4.5 V, I_D = - 0.77 A		3.5	5.5	nC
Gate-Source Charge	Q_{gs}			0.65		
Gate-Drain Charge	Q_{gd}			0.60		
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = - 10 V, R_L = 20 Ω $I_D \cong$ - 0.5 A, V_{GEN} = - 4.5 V, R_G = 6 Ω		10	20	ns
Rise Time	t_r			15	30	
Turn-Off Delay Time	$t_{d(off)}$			30	60	
Fall Time	t_f			10	20	
Source-Drain Reverse Recovery Time	t_{rr}	I_F = - 0.14 A, dI/dt = 100 A/µs		20	40	

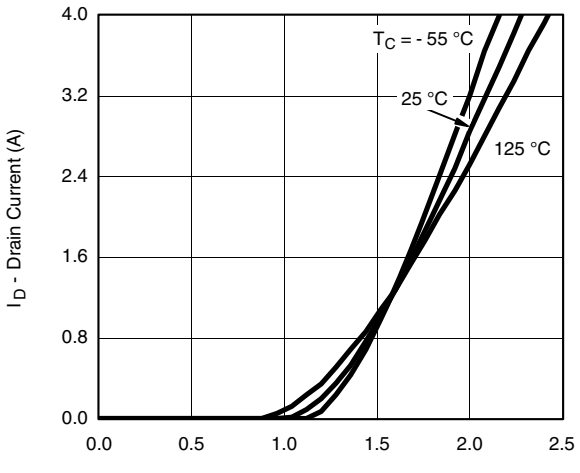
Notes:
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

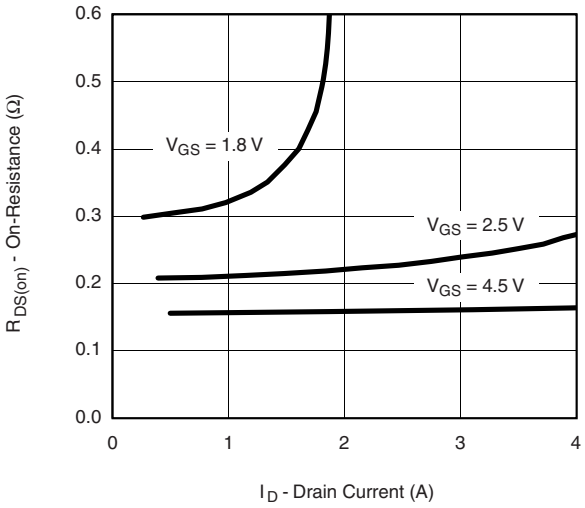


Output Characteristics

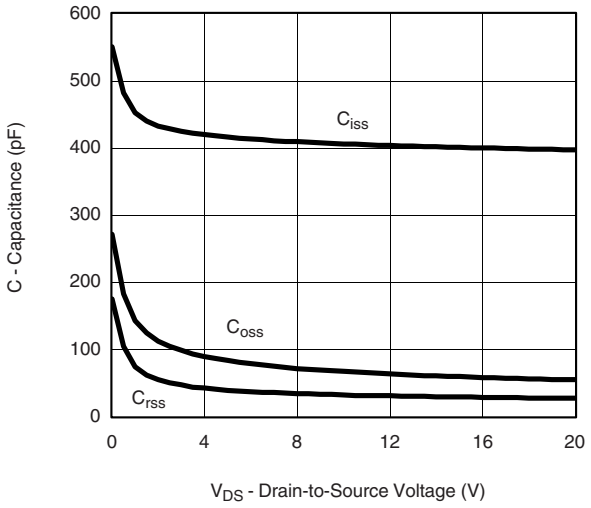


Transfer Characteristics

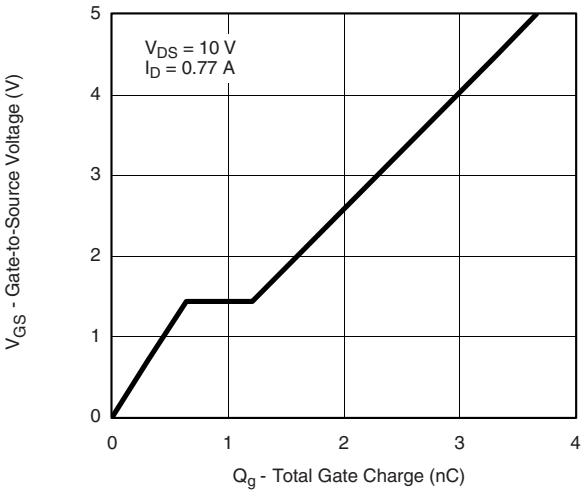
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



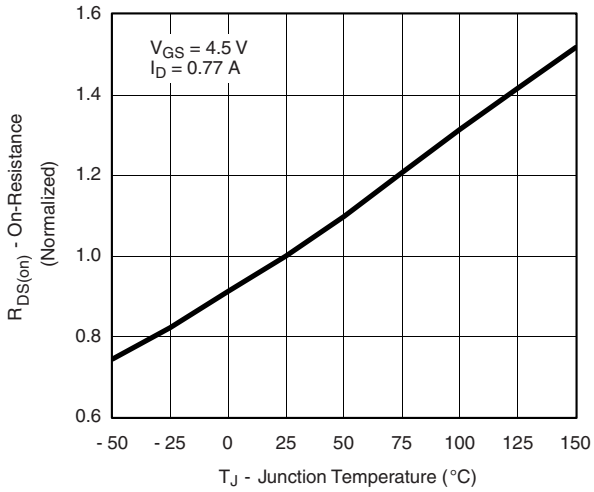
On-Resistance vs. Drain Current



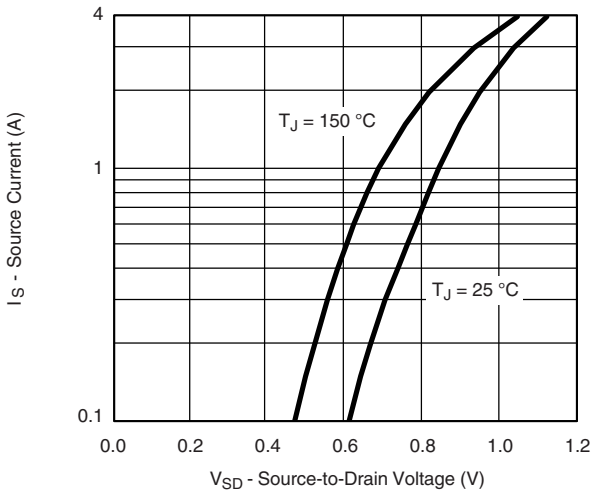
Capacitance



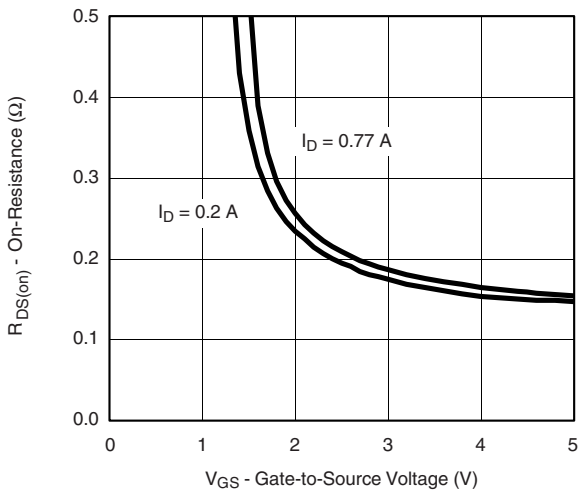
Gate Charge



On-Resistance vs. Junction Temperature

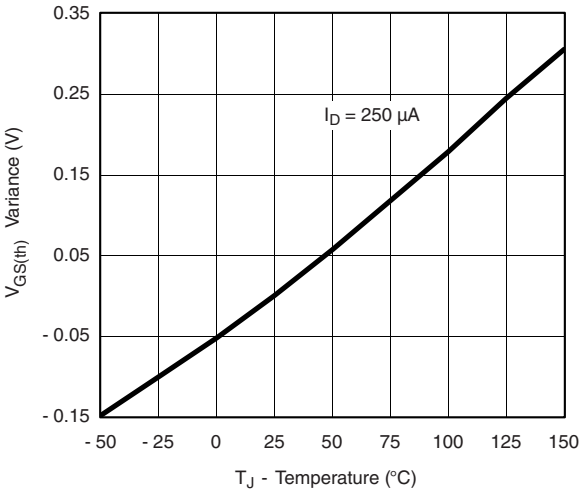


Source-Drain Diode Forward Voltage

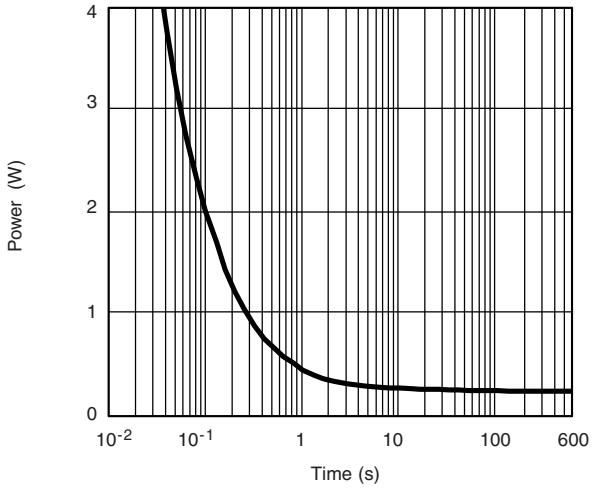


On-Resistance vs. Gate-to-Source Voltage

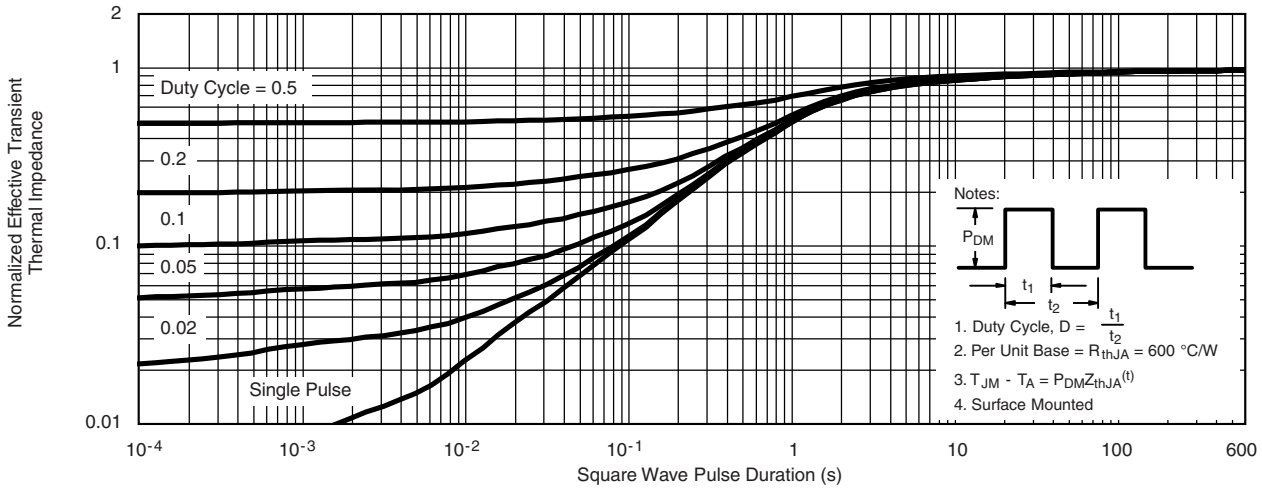
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



Threshold Voltage



Single Pulse Power, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Ambient

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